

FDMC86244

N-Channel Power Trench® MOSFET

150 V, 9.4 A, 134 mΩ

Features

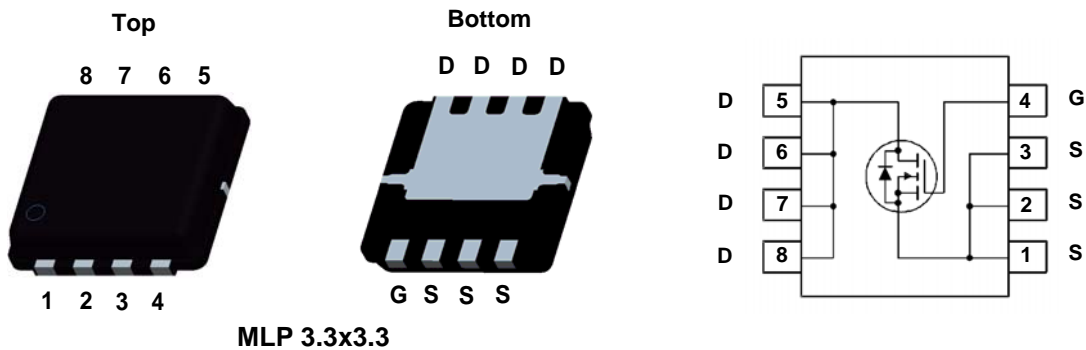
- Max $r_{DS(on)}$ = 134 mΩ at $V_{GS} = 10$ V, $I_D = 2.8$ A
- Max $r_{DS(on)}$ = 186 mΩ at $V_{GS} = 6$ V, $I_D = 2.4$ A
- Low Profile - 1 mm max in Power 33
- 100% UIL Tested
- RoHS Compliant

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC - DC Conversion



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous $T_C = 25^\circ\text{C}$	9.4	A
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	2.8	
	-Pulsed	12	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	12	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	26	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.7	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	125	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC86244	FDMC86244	Power 33	13"	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		106		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	2	2.6	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-9		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.8\text{ A}$		105	134	m Ω
		$V_{GS} = 6\text{ V}$, $I_D = 2.4\text{ A}$		120	186	
		$V_{GS} = 10\text{ V}$, $I_D = 2.8\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		199	254	
g_{FS}	Forward Transconductance	$V_{DD} = 10\text{ V}$, $I_D = 2.8\text{ A}$		8		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 75\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		257	345	pF
C_{oss}	Output Capacitance			32	45	pF
C_{rss}	Reverse Transfer Capacitance			1.8	5	pF

Switching Characteristics

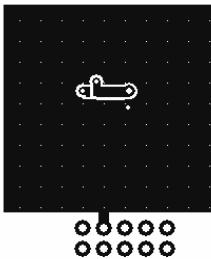
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{ V}$, $I_D = 2.8\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		5.3	11	ns	
t_r	Rise Time			1.5	10	ns	
$t_{d(off)}$	Turn-Off Delay Time			9.9	20	ns	
t_f	Fall Time			2.3	10	ns	
$Q_{g(TOT)}$	Total Gate Charge		$V_{GS} = 0\text{ V to }10\text{ V}$		4.2	5.9	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V to }5\text{ V}$	$V_{DD} = 75\text{ V}$, $I_D = 2.8\text{ A}$		2.4	3.4	
Q_{gs}	Total Gate Charge				1.1		nC
Q_{gd}	Gate to Drain "Miller" Charge				1.0		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 2.8\text{ A}$ (Note 2)		0.81	1.3	V
		$V_{GS} = 0\text{ V}$, $I_S = 2\text{ A}$ (Note 2)		0.79	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 2.8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		48	76	ns
Q_{rr}	Reverse Recovery Charge			38	61	nC

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53 $^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b. 125 $^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.
- Starting $T_J = 25\text{ }^\circ\text{C}$; N-ch: L = 1.0 mH, $I_{AS} = 5.0\text{ A}$, $V_{DD} = 135\text{ V}$, $V_{GS} = 10\text{ V}$.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

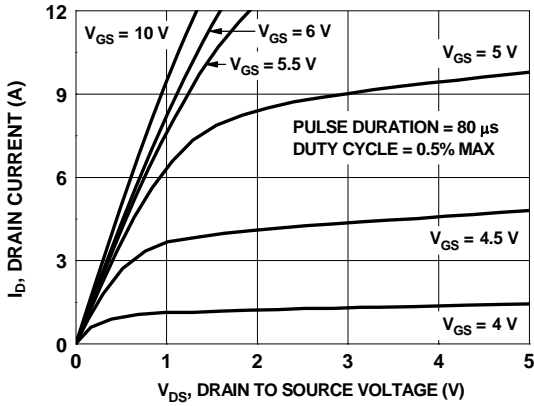


Figure 1. On Region Characteristics

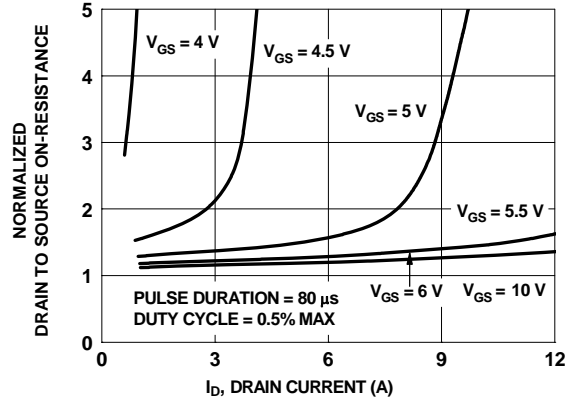


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

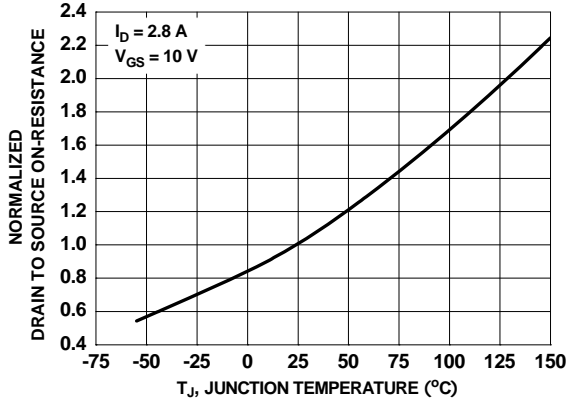


Figure 3. Normalized On Resistance vs Junction Temperature

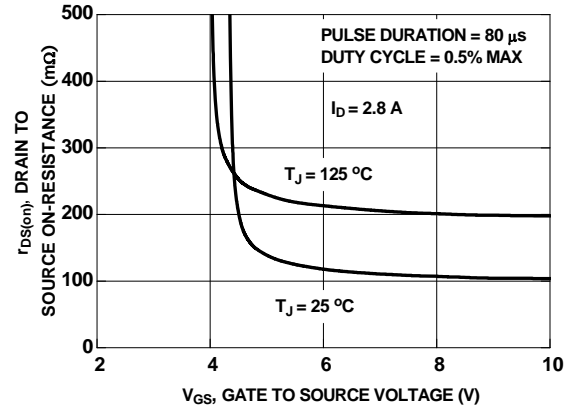


Figure 4. On-Resistance vs Gate to Source Voltage

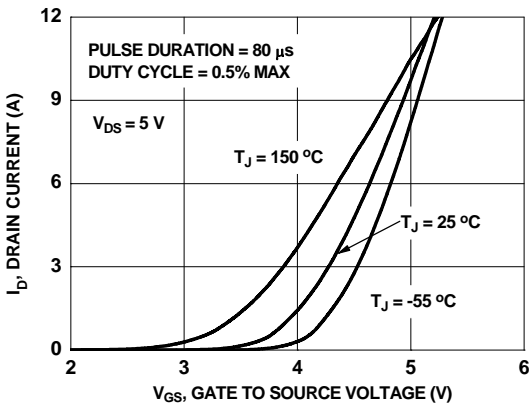


Figure 5. Transfer Characteristics

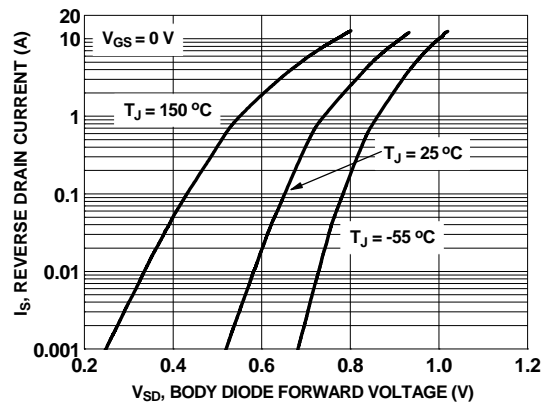


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

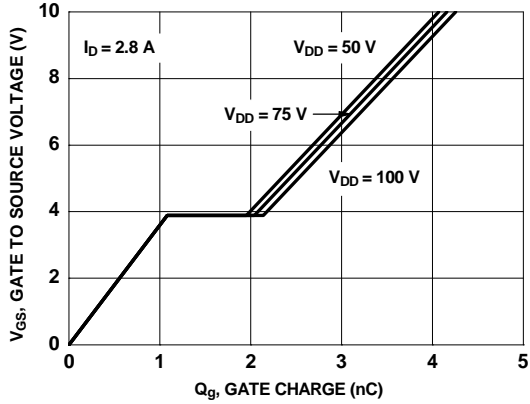


Figure 7. Gate Charge Characteristics

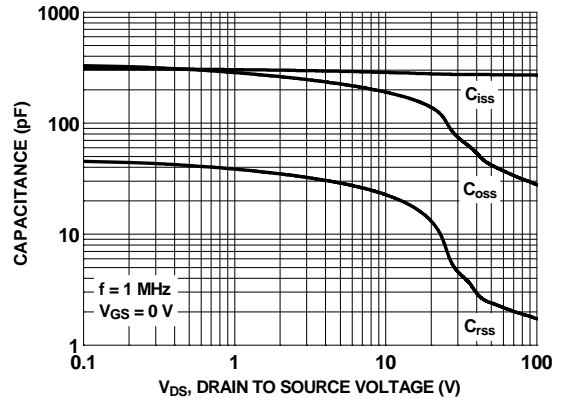


Figure 8. Capacitance vs Drain to Source Voltage

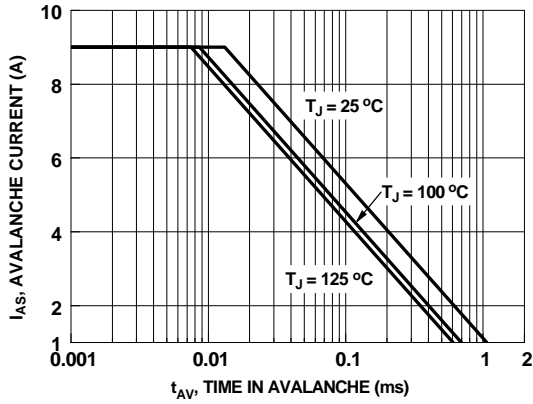


Figure 9. Unclamped Inductive Switching Capability

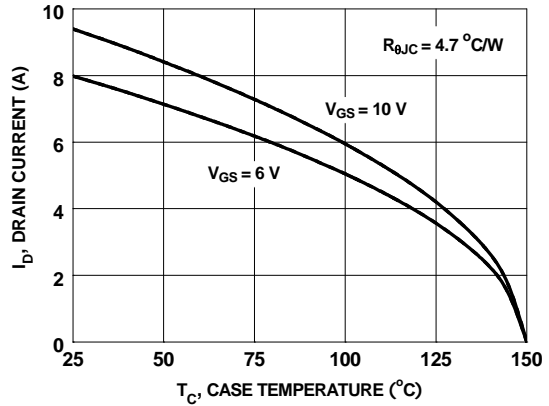


Figure 10. Maximum Continuous Drain Current vs Case Temperature

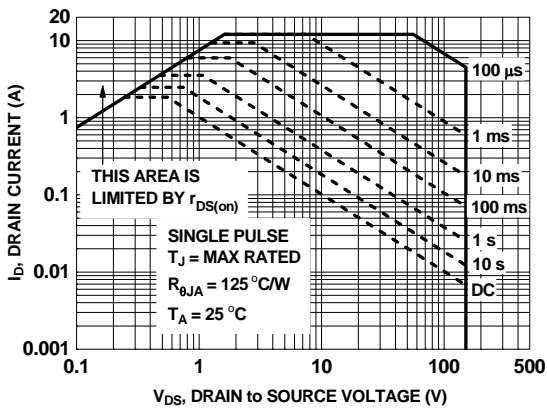


Figure 11. Forward Bias Safe Operating Area

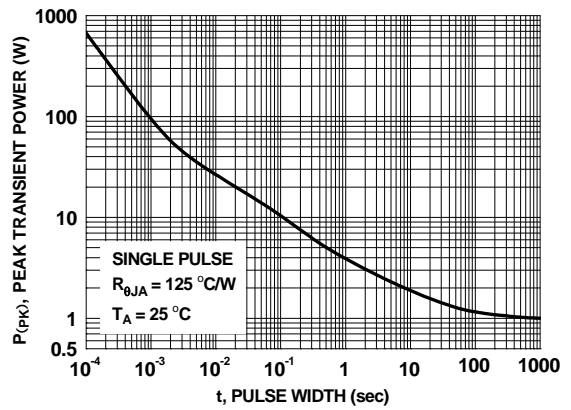


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

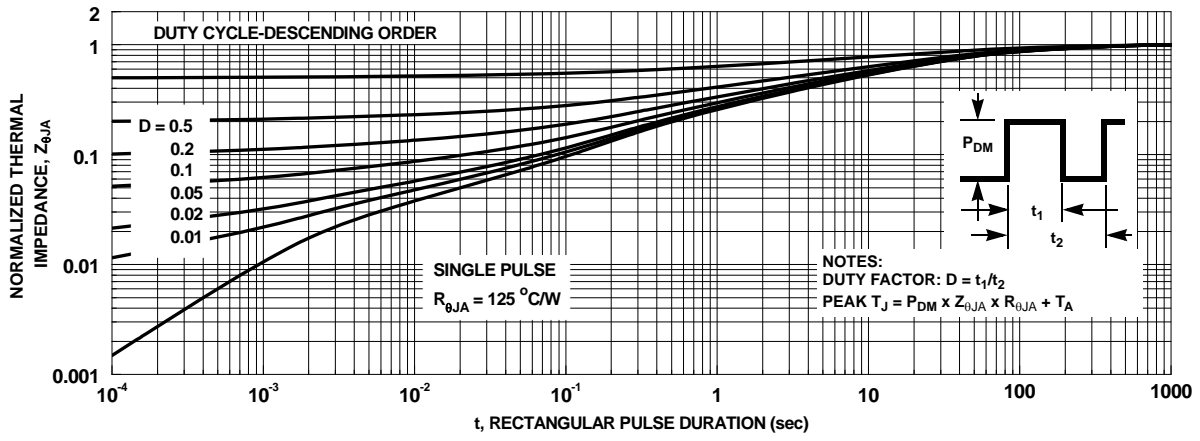
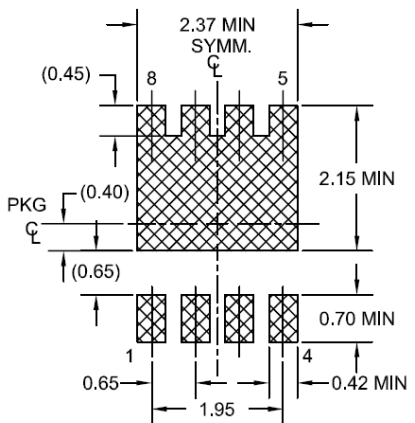
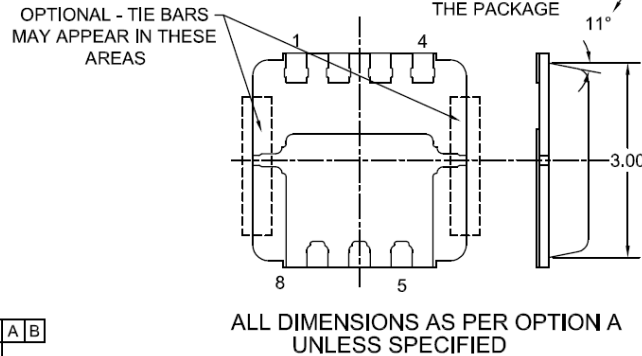
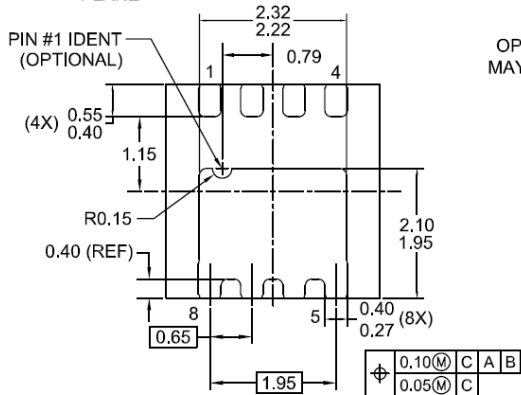
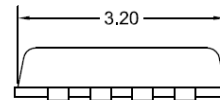
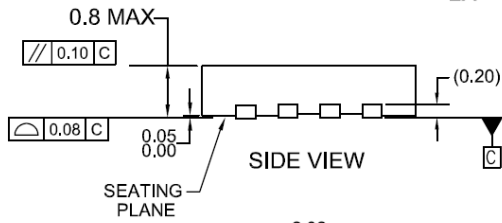
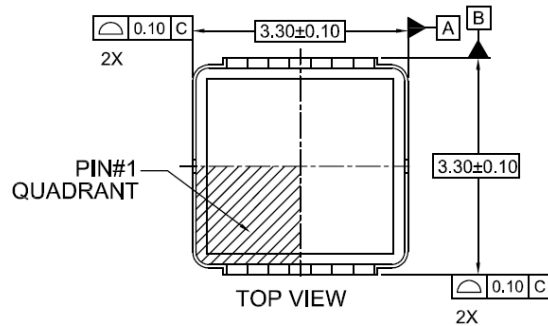
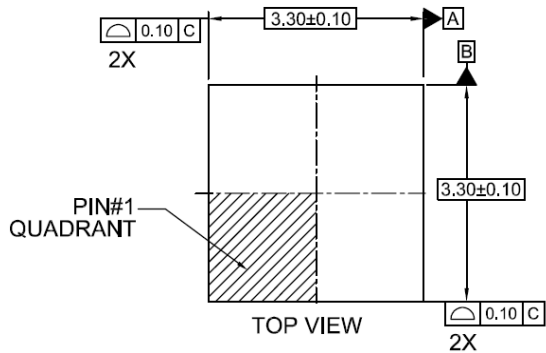


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout





NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- D. DIMENSIONS DOES NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.
- E. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.
- F. DRAWING FILENAME: MLP33-08rev1.



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